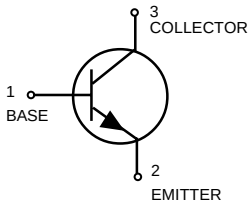
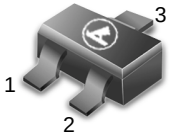
VHF/UHF Transistors



LMBTH10WT1



SC-70/SOT–323

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	25	Vdc
Collector–Base Voltage	V_{CBO}	30	Vdc
Emitter–Base Voltage	V_{EBO}	3.0	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR– 5 Board, (1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J , T_{stg}	–55 to +150	°C

DEVICE MARKING

LMBTH10WT1 = 3E

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B= 0)	$V_{(BR)CEO}$	25	—	—	Vdc
Collector–Base Breakdown Voltage (I_C = 100 µAdc , I_E = 0)	$V_{(BR)CBO}$	30	—	—	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 µAdc , I_C= 0)	$V_{(BR)EBO}$	3.0	—	—	Vdc
Collector Cutoff Current (V_{CB} = 25Vdc , I_E = 0)	I_{CBO}	—	—	100	nAdc
Emitter Cutoff Current (V_{EB} = 2.0Vdc , I_C= 0)	I_{EBO}	—	—	100	nAdc

1. FR–5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

LMBTH10WT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
DC Current Gain (I_C = 4.0 mAdc, V_{CE} = 10 Vdc)	h_{FE}	60	—	270	—
Collector–Emitter Saturation Voltage (I_C = 4.0mAdc, I_B = 0.4 mAdc)	$V_{CE(sat)}$	—	—	0.5	Vdc
Base–Emitter On Voltage (I_C = 4.0mAdc, V_{CE} = 10Vdc)	V_{BE}	—	—	0.95	Vdc
SMALL–SIGNAL CHARACTERISTICS					
Current Gain–Bandwidth Product (V_{CE} = 10 Vdc, I_C = 4.0mAdc, f = 100MHz)	f_T	650	—	—	MHz
Collector –Base Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{cb}	—	—	0.7	pF
Collector –Base Feedback Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{rb}	—	—	0.65	pF
Collector Base Time Constant (I_C = 4.0mAdc,V_{CB}=10 Vdc, f = 31.8 MHz)	rb' C_C	—	—	9.0	ps

LMBTH10WT1

TYPICAL CHARACTERISTICS

COMMON–BASE y PARAMETERS versus FREQUENCY

(V_{CB} = 10 Vdc, I C = 4.0 mAdc, T_A = 25°C)

yib , INPUT ADMITTANCE

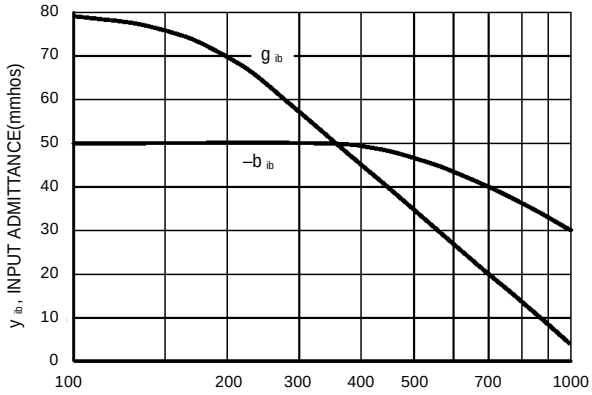


Figure 1. Rectangular Form

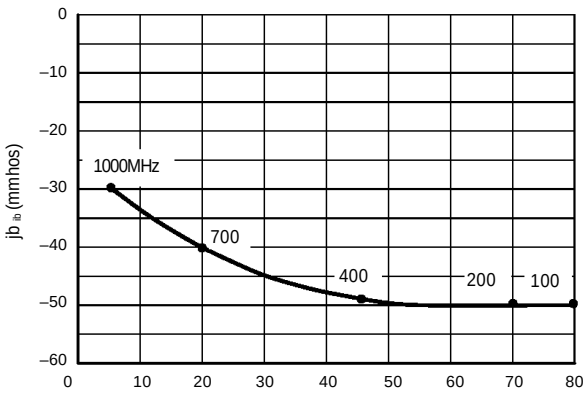


Figure 2. Polar Form

y fb , FORWARD TRANSFER ADMITTANCE

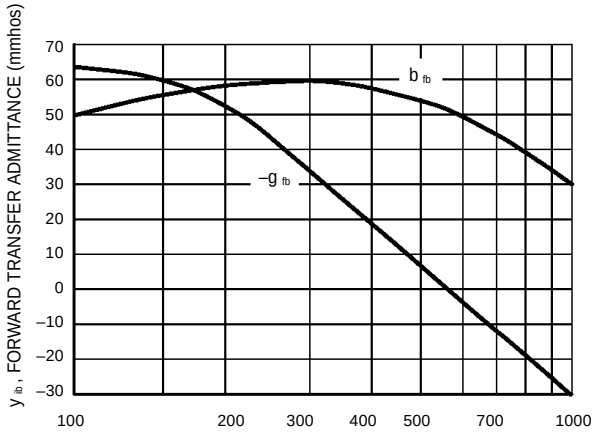


Figure 3. Rectangular Form

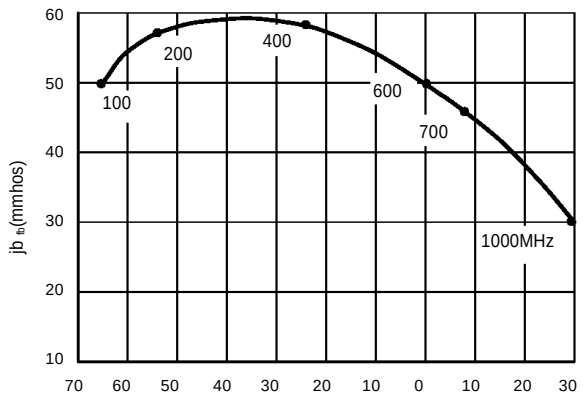


Figure 4. Polar Form

LMBTH10WT1

TYPICAL CHARACTERISTICS

COMMON–BASE y PARAMETERS versus FREQUENCY
(V_{CB} = 10 Vdc, I_C = 4.0 mAdc, T_A = 25°C)
y_{rb}, REVERSE TRANSFER ADMITTANCE

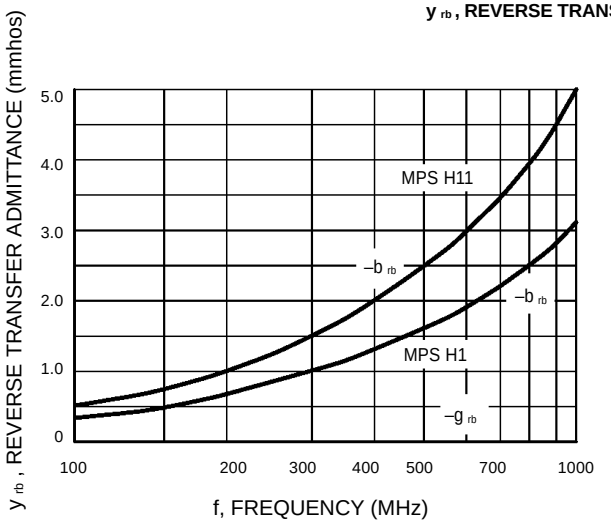


Figure 5. Rectangular Form

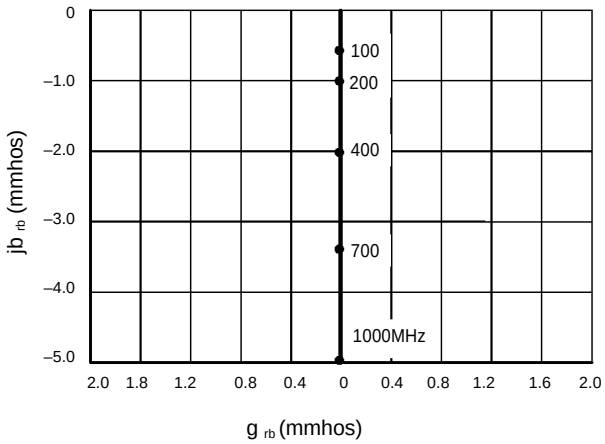


Figure 6. Polar Form

y_{ob}, OUTPUT ADMITTANCE

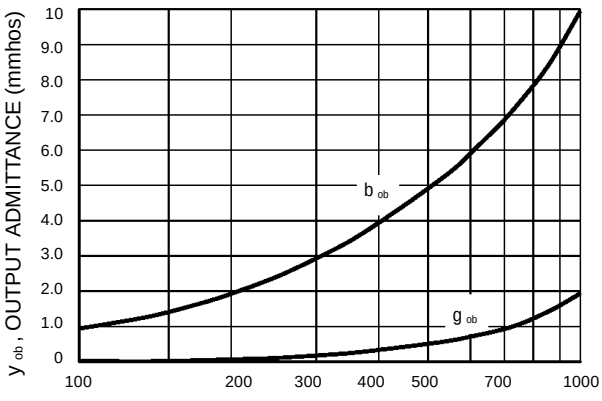


Figure 7. Rectangular Form

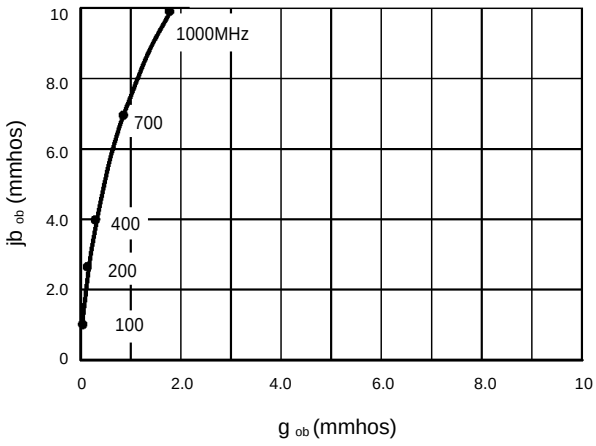


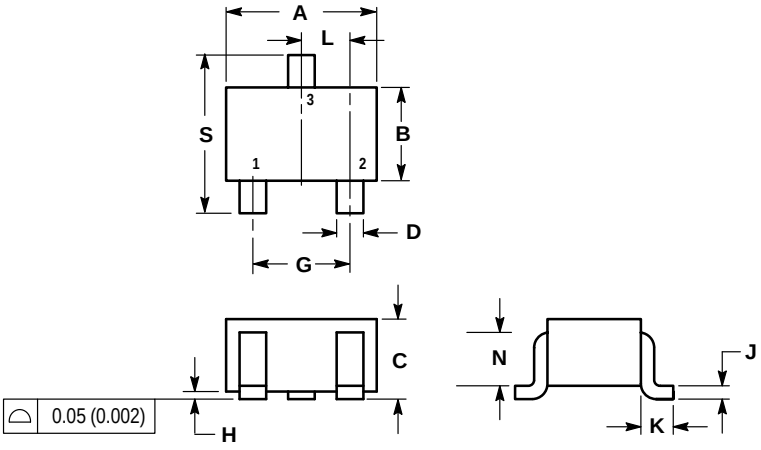
Figure 8. Polar Form

LMBTH10WT1

SC−70 / SOT−323

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40



PIN 1. BASE
2. EMITTER
3. COLLECTOR